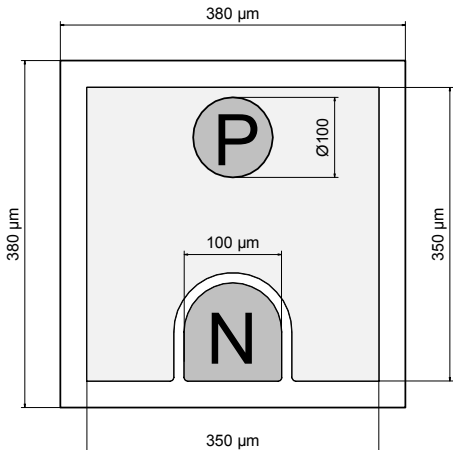


Radiation	Type	Technology	Electrodes
Green	Standard	InGaN/Al <sub>2</sub> O <sub>3</sub>	Both on top side

	typ. dimensions in µm (±20 µm)
	<p>typ. thickness 90 (±20) µm</p> <p>front side metalization Au-alloy, 0.5 µm</p> <p>backside metalization Al-alloy, 1.5 µm</p>

### Maximum Ratings

T<sub>amb</sub> = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)		I <sub>F</sub>	20	mA
Peak forward current	(t <sub>p</sub> ≤ 50 µs, t <sub>p</sub> /T = 1/2)	I <sub>FM</sub>	100	mA
Operating temperature range		T <sub>amb</sub>	-40 to +85	°C
Storage temperature range		T <sub>stg</sub>	-40 to +100	°C

### Optical and Electrical Characteristics

T<sub>amb</sub> = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I <sub>F</sub> = 20 mA	V <sub>F</sub>		3.3	3.5	V
Reverse voltage	I <sub>F</sub> = 1 µA	V <sub>R</sub>	5			V
Luminous intensity <sup>1</sup>	I <sub>F</sub> = 20 mA	I <sub>v</sub>	220	280		mcd
Dominant wavelength	I <sub>F</sub> = 20 mA	λ <sub>D</sub>	480	490	500	nm
Spectral bandwidth at 50%	I <sub>F</sub> = 20 mA	Δλ <sub>0.5</sub>		25		nm
Switching time	I <sub>F</sub> = 20 mA	t <sub>r</sub> , t <sub>f</sub>		20		ns

<sup>1</sup>Measured on bare chip on TO-18 header with *EPIGAP* equipment

### Labeling

Type	Lot N°	I <sub>v</sub> (typ) [mcd]	V <sub>F</sub> (typ) [V]	Quantity
ELC-490-37				

**Packing:** Chips on adhesive film with wire-bond side on top